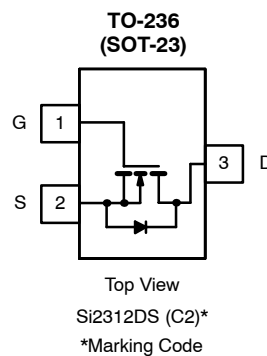




N-Channel 20-V (D-S) MOSFET

1.8-V Rated

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.033 @ $V_{GS} = 4.5$ V	4.9
	0.040 @ $V_{GS} = 2.5$ V	4.4
	0.051 @ $V_{GS} = 1.8$ V	3.9



Ordering Information: Si2312DS-T1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	4.9	3.77	A
	$T_A = 70^\circ\text{C}$		3.9	3.0	
Pulsed Drain Current ^b		I_{DM}	15		
Avalanche Current ^b		I_{AS}	15		
Single Avalanche Energy		E_{AS}	11.25		mJ
			L = 0.1 mH		
Continuous Source Current (Diode Conduction) ^a		I_S	1.0		A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	1.25	0.75	W
	$T_A = 70^\circ\text{C}$		0.80	0.48	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	75	100	$^\circ\text{C}/\text{W}$
	Steady State		120	166	
Maximum Junction-to-Foot	Steady State	R_{thJF}	40	50	

Notes

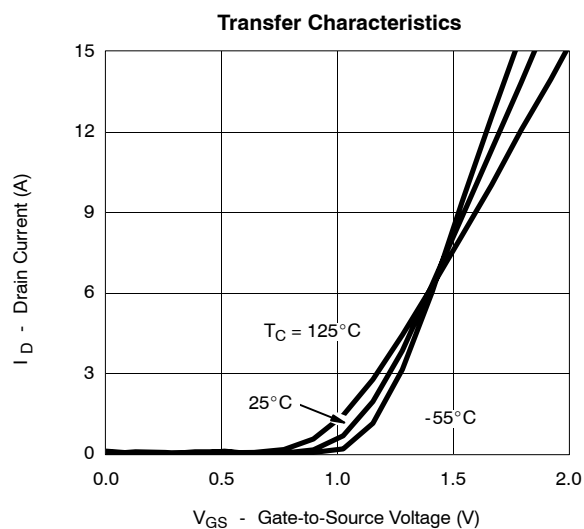
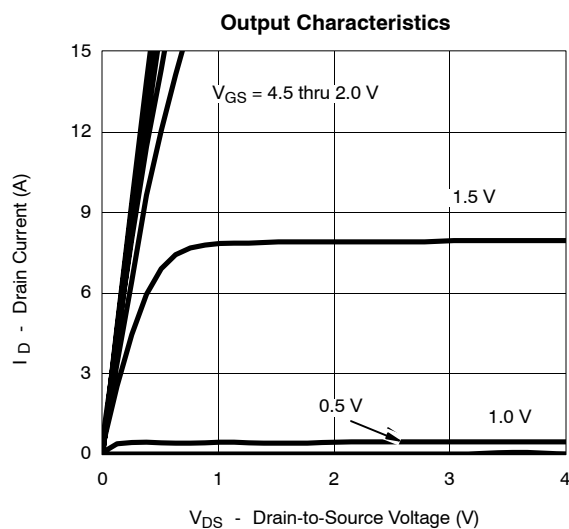
- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.45	0.65	0.85	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70^\circ\text{C}$			75	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		0.027	0.033	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 4.5\text{ A}$		0.033	0.040	
		$V_{GS} = 1.8\text{ V}, I_D = 4.0\text{ A}$		0.042	0.051	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5.0\text{ A}$		40		S
Diode Forward Voltage	V_{SD}	$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		11.2	14.0	nC
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.2		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\ \Omega$ $I_D \cong 1.0\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 6\ \Omega$		15	25	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			48	70	
Fall-Time	t_f			31	45	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		13	25	

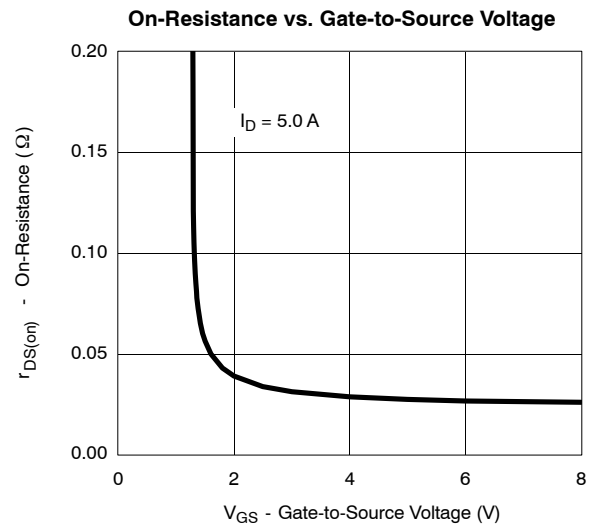
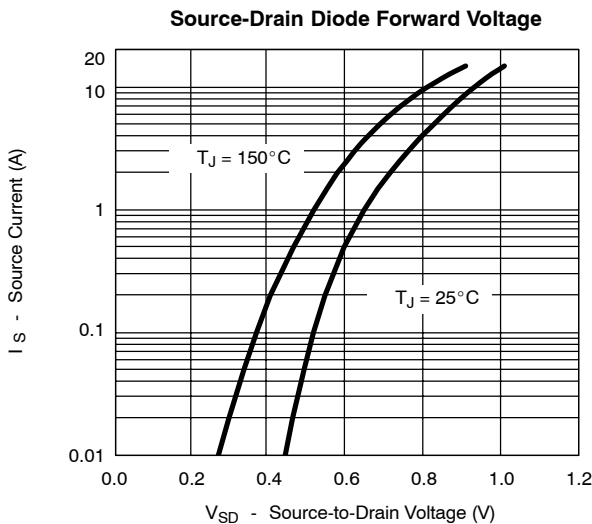
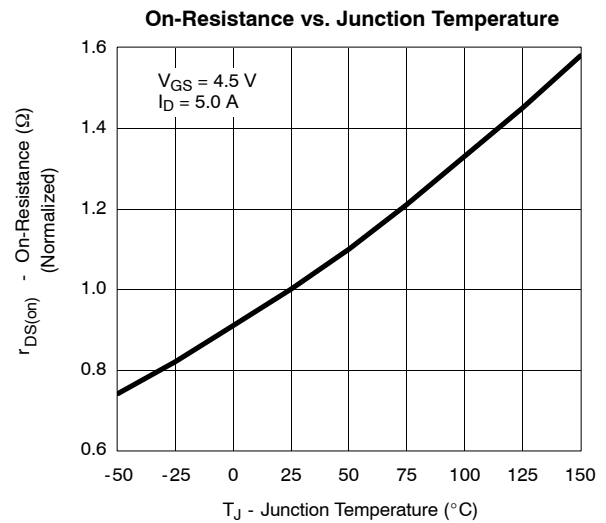
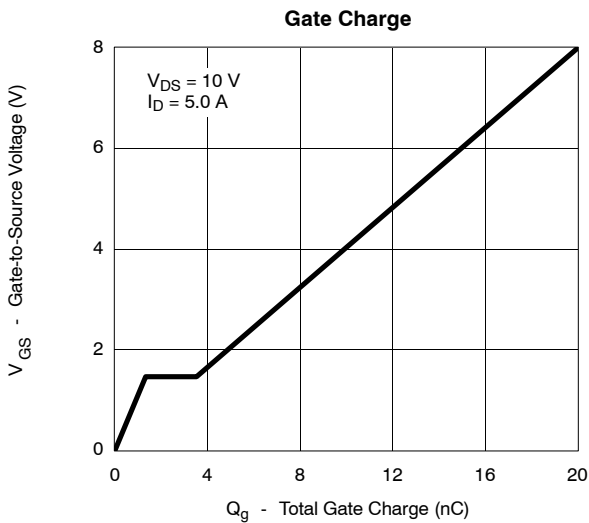
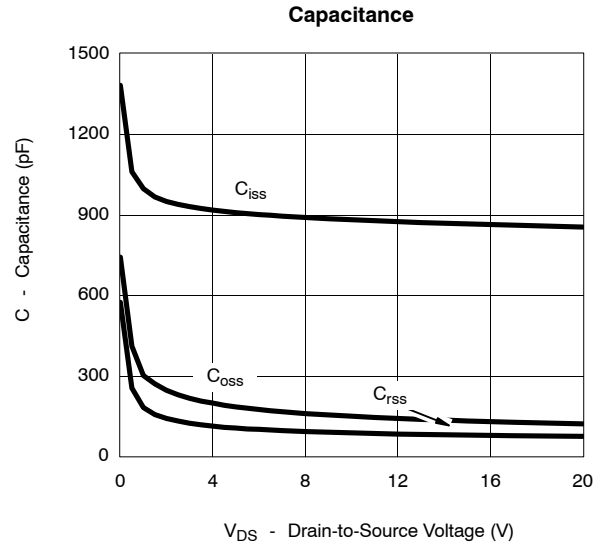
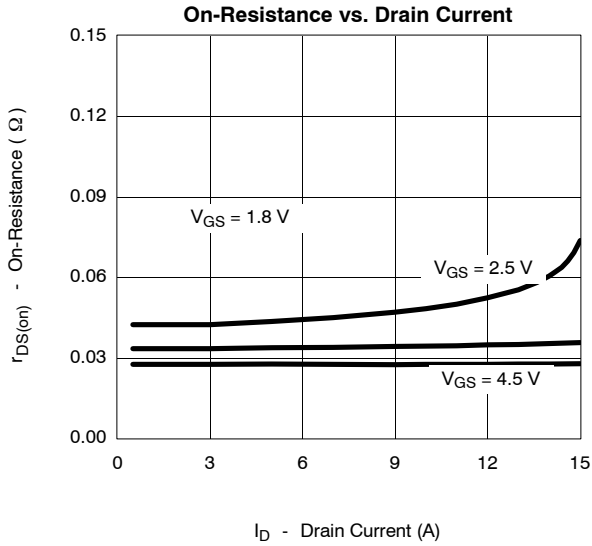
Notes

- a. Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

